PD - 95566A

International
IOR Rectifier

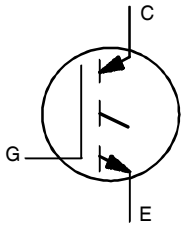
IRG4PC60FPbF

INSULATED GATE BIPOLAR TRANSISTOR

Fast Speed IGBT

Features

- Fast: Optimized for medium operating frequencies (1-5 kHz in hard switching, >20 kHz in resonant mode).
- Generation 4 IGBT design provides tighter parameter distribution and higher efficiency.
- Industry standard TO-247AC package.
- Lead-Free



n-channel

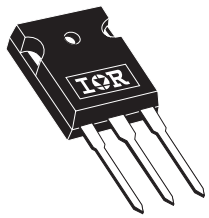
$V_{CES} = 600V$

$V_{CE(on)}$ typ. = 1.50V

@V_{GE} = 15V, I_C = 60A

Benefits

- Generation 4 IGBT's offer highest efficiency available
- IGBT's optimized for specified application conditions
- Designed for best performance when used with IR Hexfred & IR Fred companion diodes.



TO-247AC

Absolute Maximum Ratings

	Parameter	Max.	Units
V_{CES}	Collector-to-Emitter Breakdown Voltage	600	V
I_C @ T_C = 25°C	Continuous Collector Current	90	A
I_C @ T_C = 100°C	Continuous Collector Current	60	
I_{CM}	Pulsed Collector Current ①	360	
I_{LM}	Clamped Inductive Load Current ②	360	
V_{GE}	Gate-to-Emitter Voltage	± 20	V
E_{ARV}	Reverse Voltage Avalanche Energy ③	200	mJ
P_D @ T_C = 25°C	Maximum Power Dissipation	520	W
P_D @ T_C = 100°C	Maximum Power Dissipation	210	
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to + 150	°C
	Soldering Temperature, for 10 seconds	300 (0.063 in. (1.6mm from case)	
	Mounting torque, 6-32 or M3 screw.	10 lbf•in (1.1N•m)	

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	–––	0.24	°C/W
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface	0.24	–––	
$R_{\theta JA}$	Junction-to-Ambient, typical socket mount	–––	40	
Wt	Weight	6 (0.21)	–––	g (oz)

12/04/09

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage	600	—	—	V	V_{GE} = 0V, I_C = 250µA
$V_{(BR)ECS}$	Emitter-to-Collector Breakdown Voltage ④	16	—	—	V	V_{GE} = 0V, I_C = 1.0A
$\Delta V_{(BR)CES}/\Delta T_J$	Temperature Coeff. of Breakdown Voltage	—	0.13	—	V/°C	V_{GE} = 0V, I_C = 1.0mA
$V_{CE(ON)}$	Collector-to-Emitter Saturation Voltage	—	1.5	1.8	V	I_C = 60A V_{GE} = 15V
		—	1.7	—		I_C = 90A See Fig.2, 5
		—	1.5	—		I_C = 60A , T_J = 150°C
$V_{GE(th)}$	Gate Threshold Voltage	3.0	—	6.0		V_{CE} = V_{GE}, I_C = 250µA
$\Delta V_{GE(th)}/\Delta T_J$	Temperature Coeff. of Threshold Voltage	—	-11	—	mV/°C	V_{CE} = V_{GE}, I_C = 250µA
g_{fe}	Forward Transconductance ⑤	36	69	—	S	V_{CE} = 100V, I_C = 60A
I_{CES}	Zero Gate Voltage Collector Current	—	—	250	µA	V_{GE} = 0V, V_{CE} = 600V
		—	—	2.0		V_{GE} = 0V, V_{CE} = 10V, T_J = 25°C
		—	—	1000		V_{GE} = 0V, V_{CE} = 600V, T_J = 150°C
I_{GES}	Gate-to-Emitter Leakage Current	—	—	±100	nA	V_{GE} = ±20V

Switching Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
Q_g	Total Gate Charge (turn-on)	—	290	340	nC	I_C = 40A
Q_{ge}	Gate - Emitter Charge (turn-on)	—	40	47		V_{CC} = 400V See Fig. 8
Q_{gc}	Gate - Collector Charge (turn-on)	—	100	130		V_{GE} = 15V
$t_{d(on)}$	Turn-On Delay Time	—	42	—	ns	
t_r	Rise Time	—	66	—		T_J = 25°C
$t_{d(off)}$	Turn-Off Delay Time	—	310	360		I_C = 60A, V_{CC} = 480V
t_f	Fall Time	—	170	220		V_{GE} = 15V, R_G = 5.0Ω
E_{on}	Turn-On Switching Loss	—	0.30	—	mJ	Energy losses include "tail"
E_{off}	Turn-Off Switching Loss	—	4.6	—		See Fig. 10, 11, 13, 14
E_{ts}	Total Switching Loss	—	4.9	6.3		
$t_{d(on)}$	Turn-On Delay Time	—	39	—	ns	T_J = 150°C,
t_r	Rise Time	—	66	—		I_C = 60A, V_{CC} = 480V
$t_{d(off)}$	Turn-Off Delay Time	—	470	—		V_{GE} = 15V, R_G = 5.0Ω
t_f	Fall Time	—	300	—		Energy losses include "tail"
E_{ts}	Total Switching Loss	—	8.8	—	mJ	See Fig. 13, 14
L_E	Internal Emitter Inductance	—	13	—	nH	Measured 5mm from package
C_{ies}	Input Capacitance	—	6050	—	pF	V_{GE} = 0V
C_{oes}	Output Capacitance	—	360	—		V_{CC} = 30V See Fig. 7
C_{res}	Reverse Transfer Capacitance	—	66	—		f = 1.0MHz

Notes:

① Repetitive rating; V_{GE} = 20V, pulse width limited by max. junction temperature. (See fig. 13b)

② V_{CC} = 80%(V_{CES}), V_{GE} = 20V, L = TBD µH, R_G = 5.0Ω. (See fig. 13a)

③ Repetitive rating; pulse width limited by maximum junction temperature.

④ Pulse width ≤ 80µs; duty factor ≤ 0.1%.

⑤ Pulse width 5.0µs, single shot.

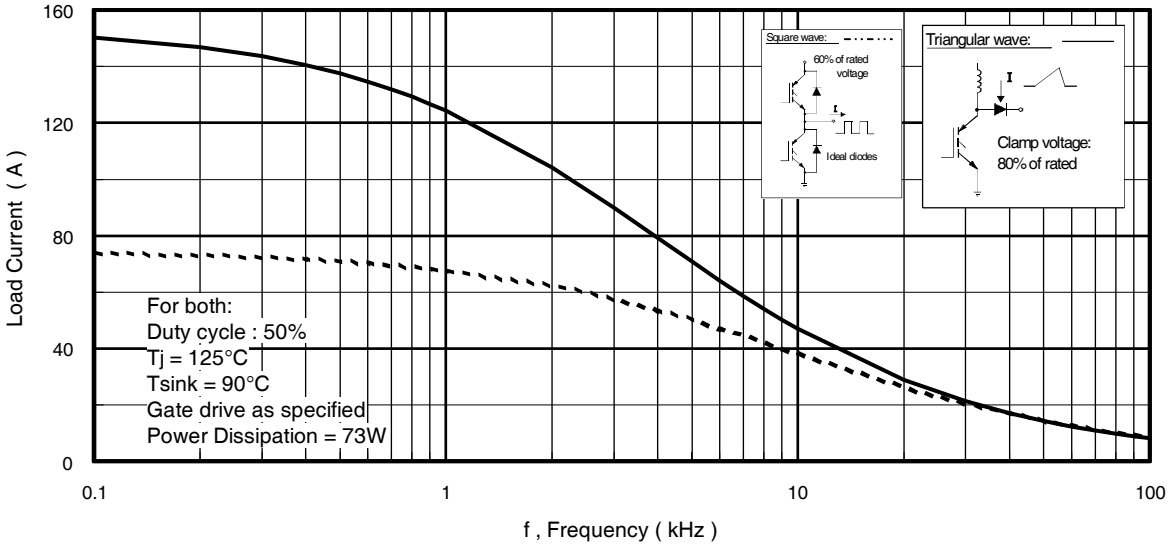


Fig. 1 - Typical Load Current vs. Frequency
(For square wave, $I=I_{RMS}$ of fundamental; for triangular wave, $I=I_{PK}$)

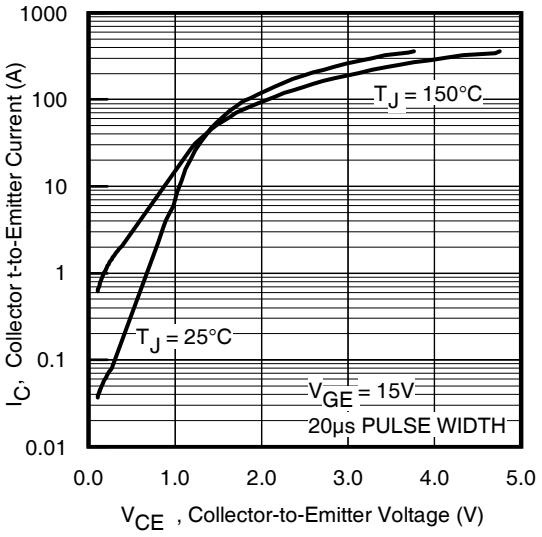


Fig. 2 - Typical Output Characteristics

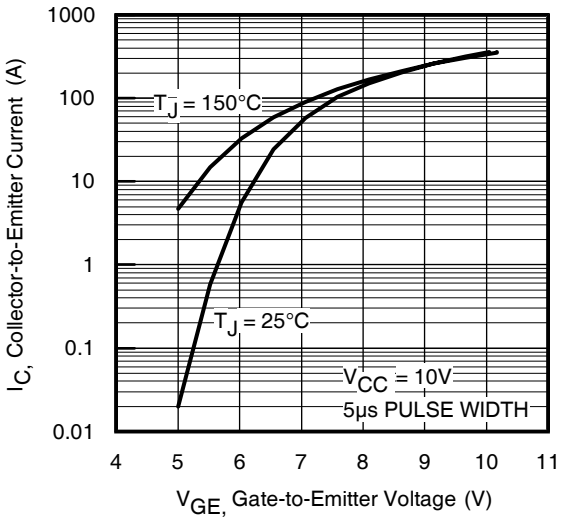


Fig. 3 - Typical Transfer Characteristics

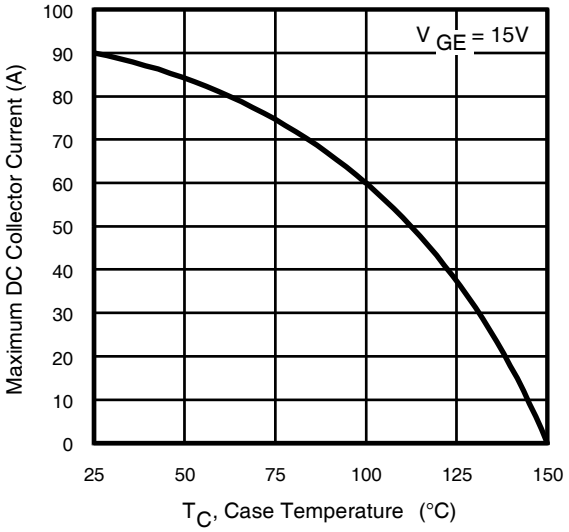


Fig. 4 - Maximum Collector Current vs. Case Temperature

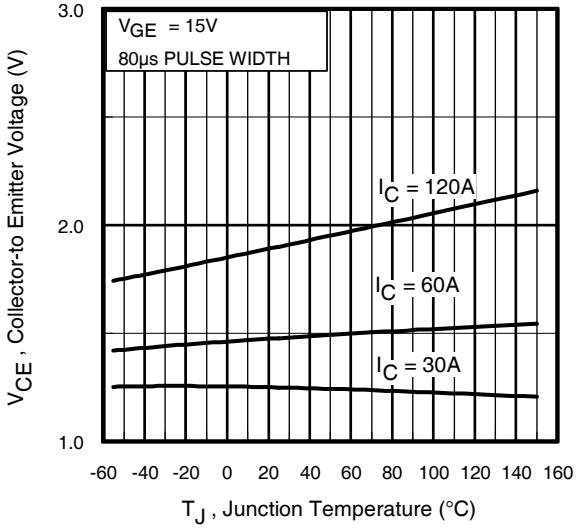


Fig. 5 - Typical Collector-to-Emitter Voltage vs. Junction Temperature

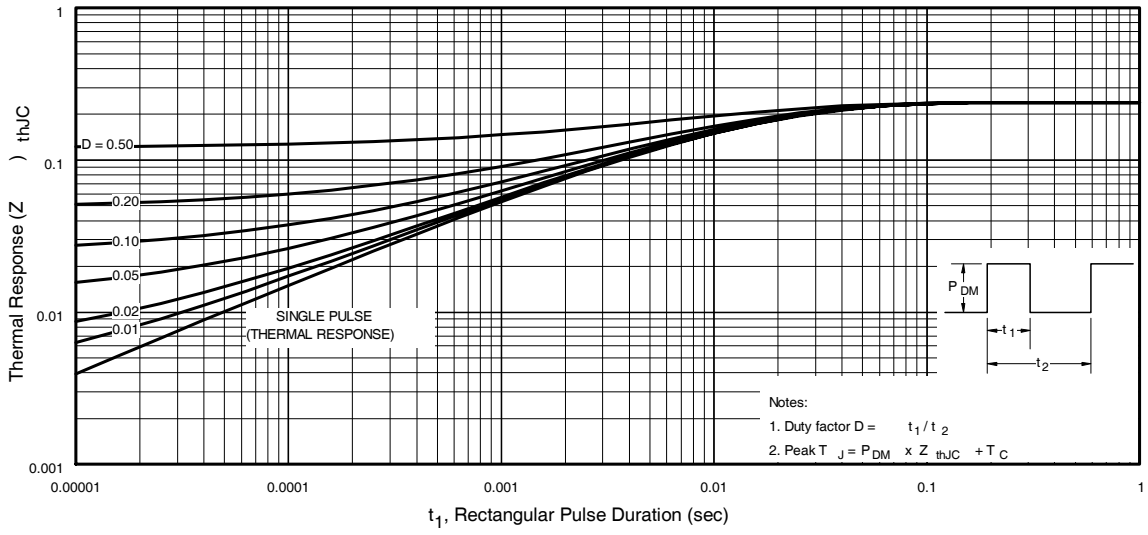


Fig. 6 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

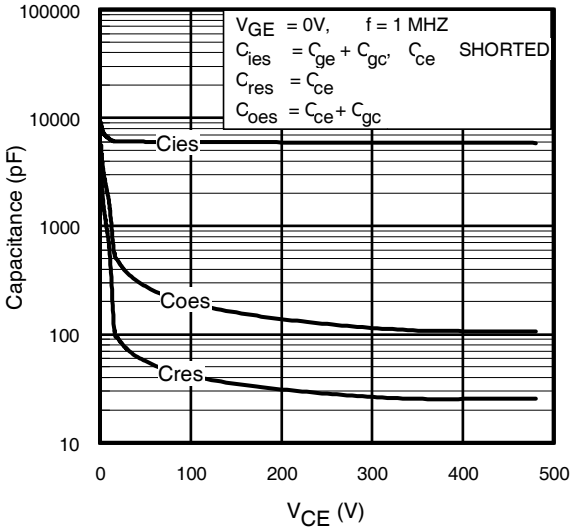


Fig. 7 - Typical Capacitance vs. Collector-to-Emitter Voltage

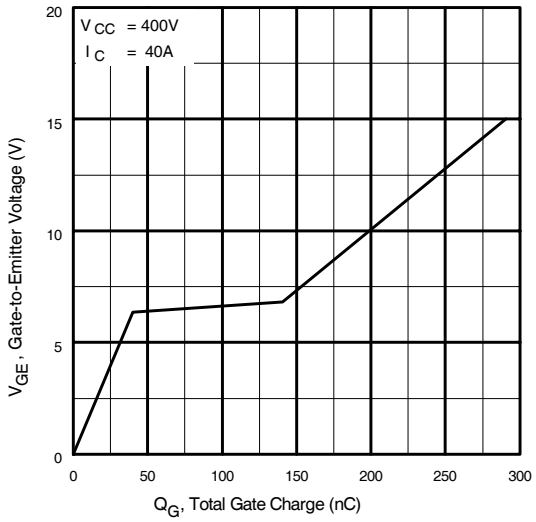


Fig. 8 - Typical Gate Charge vs. Gate-to-Emitter Voltage

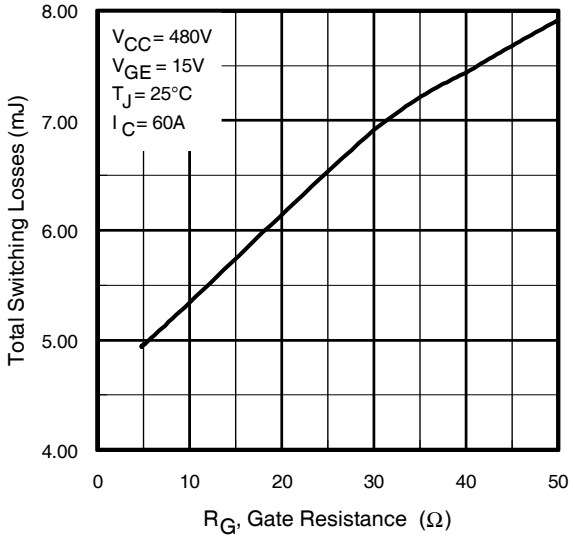


Fig. 9 - Typical Switching Losses vs. Gate Resistance

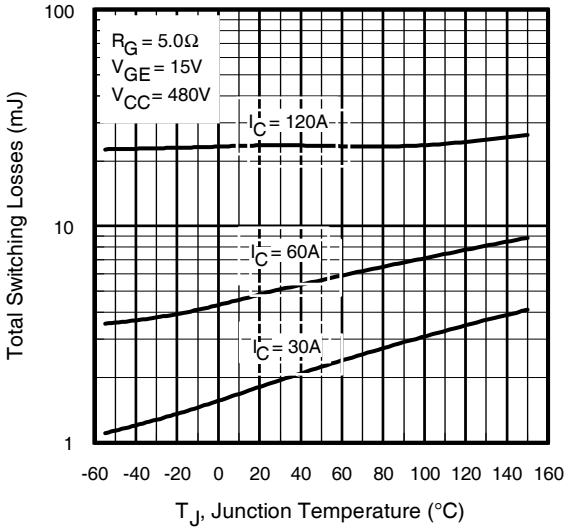


Fig. 10 - Typical Switching Losses vs. Junction Temperature

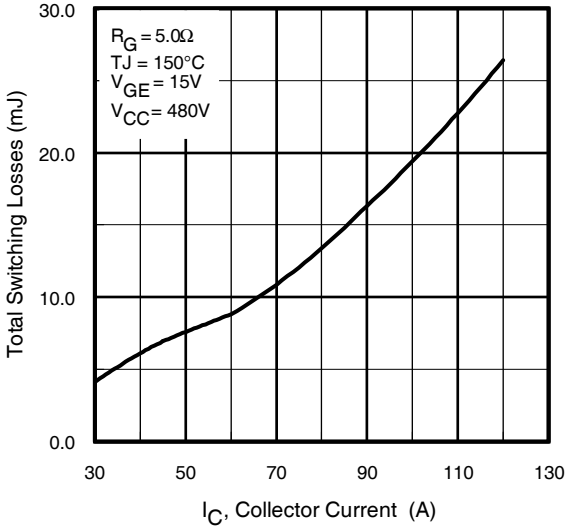


Fig. 11 - Typical Switching Losses vs. Collector-to-Emitter Current

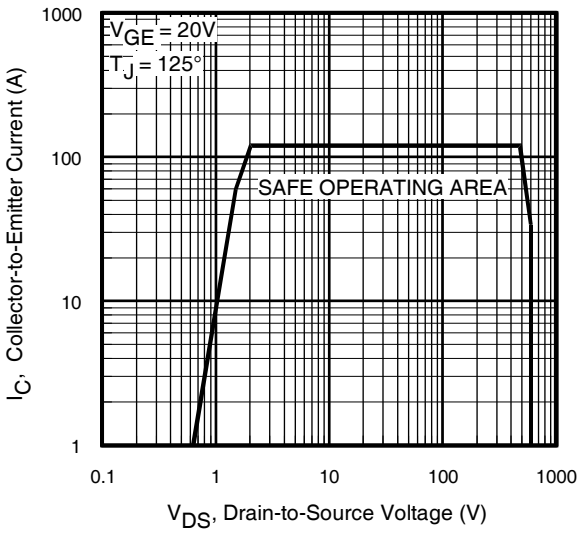


Fig. 12 - Turn-Off SOA

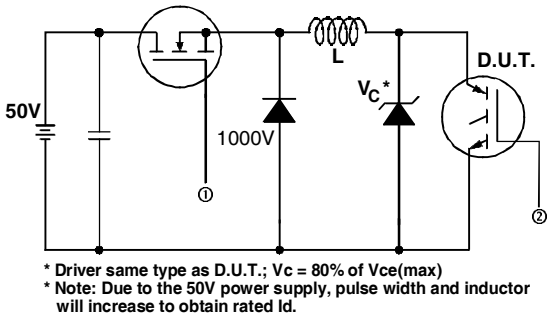


Fig. 13a - Clamped Inductive Load Test Circuit

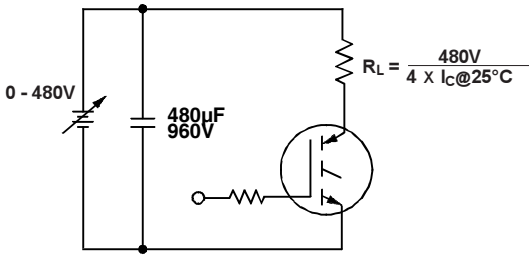


Fig. 13b - Pulsed Collector Current Test Circuit

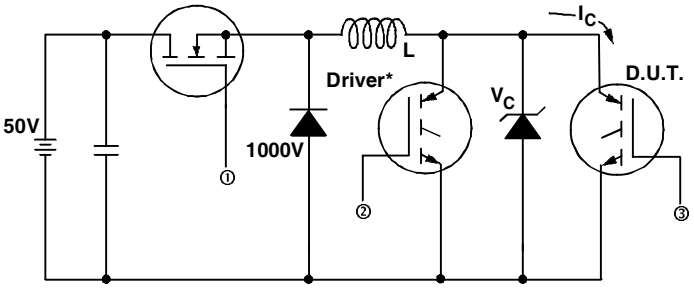


Fig. 14a - Switching Loss Test Circuit

*** Driver same type as D.U.T., VC = 480V**

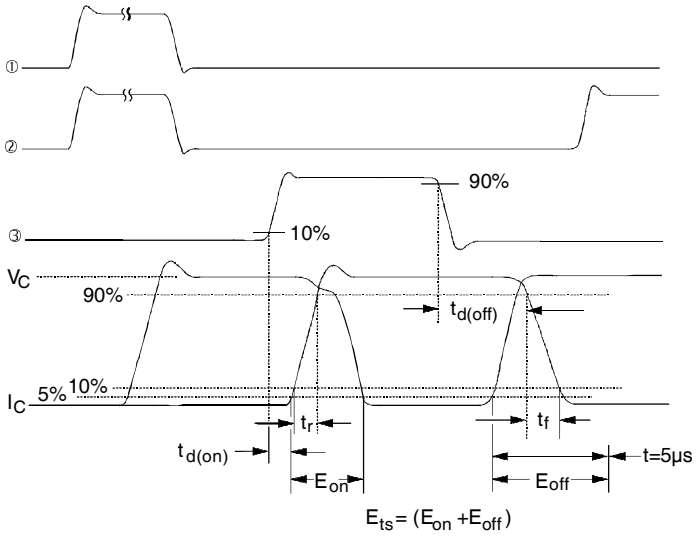
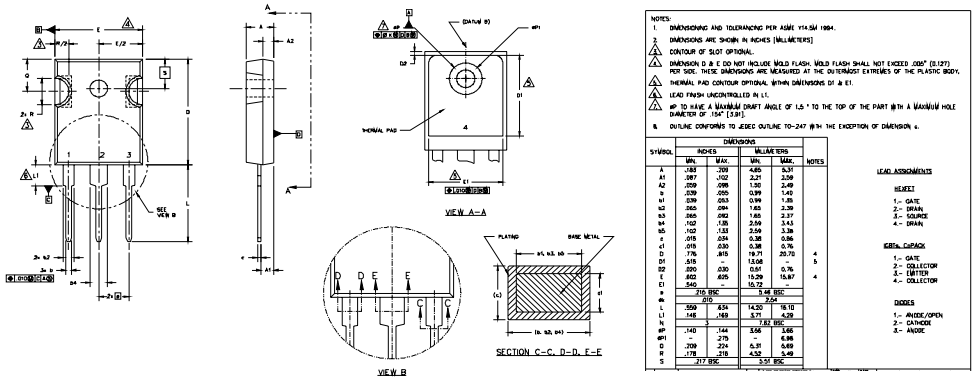


Fig. 14b - Switching Loss Waveforms

TO-247AC Package Outline

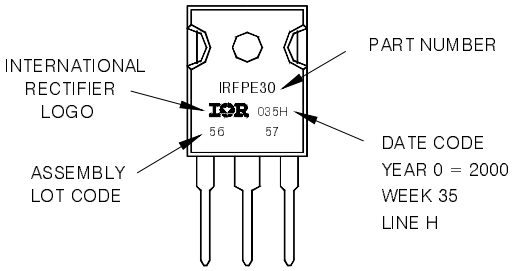
Dimensions are shown in millimeters (inches)



TO-247AC Part Marking Information

EXAMPLE: THIS IS AN IRFPE30
WITH ASSEMBLY
LOT CODE 5657
ASSEMBLED ON WW 35, 2000
IN THE ASSEMBLY LINE "H"

Note: "P" in assembly line position indicates "Lead-Free"



Note: For the most current drawing please refer to IR website at http://www.irf.com/package/

Data and specifications subject to change without notice.
This product has been designed and qualified for the Industrial market.
Qualification Standards can be found on IR's Web site.

International
IOR Rectifier

IR WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105
TAC Fax: (310) 252-7903
Visit us at www.irf.com for sales contact information.12/09